

What is claimed is:

1. A method for manufacturing light-emitting device with compound semiconductor comprising; a first step of forming n-semiconductor layer, an activated layer, and p-semiconductor layer, in order, on the top of a double substrate,

a second step of making at least a part of the n-semiconductor exposed by mesa-cut in vertical direction from a p-semiconductor layer to a part of the n-semiconductor,

a third step of forming a transparent electrode for extending an electric current on the top of the p-semiconductor layer and activating the p-semiconductor layer under the condition of an oxygen plasma, and

a fourth step of forming each of n- pad electrode and p-pad electrode on the top of the transparent electrode for extending an electric current.

2. The method for manufacturing light-emitting device with compound semiconductor of claim 1, wherein said double substrate is a sapphire substrate.

3. The method for manufacturing light-emitting device with compound semiconductor of claim 1, wherein one or more of the said n-semiconductor and p-semiconductor layer is Group III-V compound semiconductor layer.